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GUNN DIODES AND DEVICES
(BIBLIOGRAPHY FOR 1978-1980)

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16. Abstract:
This bibliography contains about 500 works on Gunn diodes and devices based on them; these references were published in Soviet and foreign scientific literature from the beginning of 1978 to the middle of 1980. Besides the publications which apply directly to the subject, the bibliography includes works in which various questions pertinent to all (or several) types of semiconductor instruments in the superhigh frequency range are mentioned including Gunn diodes.

The works are in alphabetical order by author beginning with the Russian and then going on to foreign languages. An address is given for abstracts in the Russian language, Rzh, and in the English language, EEA, for obtaining a bibliographic description. A list is given of certain abbreviations. A subject index is given at the end of the bibliography to make a subject search easier.

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List of Some Abbreviations

DC(GDG/UDG) - Gunn diode (generator/amplifier for DG)

MEP - Interline electron transfer

ONOZ - Finite accumulation of volumetric charge

RZhR(RZhF/RZhE) 80-5D125 - Abstract journal Radiotekhnika (Fizika/Electronika), 80 - year, 5 - number RZh, D - section in RZh, 125 - series number of abstract in sections (VINITI)

EI - Quick-information (VINITI)

EEA - Electrical and Electronics Abstracts (Science Abstracts, Ser. B)

EMC - European Microwave Conference

IEDM - International Electron Devices Meeting

LSA - Limited Space Accumulation

MTT-S - International Microwave Symposium

NTIS - National Technical Information Service

TE - (TEA/TEO/TELD) - Transferred Electron (TE Amplifier/Oscillator/Logic Device)

STAR - Scientific and Technical Aerospace Reports

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SUBJECT INDEX